# 1A, 30V Schottky Full Bridge

These full bridge Schottky barrier diodes are designed for the rectification of the high speed signal of wireless charging. The NSR1030QMUTAG has a very low forward voltage that will reduce conduction loss. It is housed in a UDFN 3.0 x 3.0 x 0.5 mm package that is ideal for space constrained wireless applications.

#### **Features**

- Extremely Fast Switching Speed
- Low Forward Voltage -0.49 V (Typ) @  $I_F = 1 \text{ A}$
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

## **Typical Applications**

• Low Voltage Full Bridge Rectification & Wireless Charging

## MAXIMUM RATINGS (T<sub>J</sub> = 125°C unless otherwise noted) (Note 1)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Forward Current (DC)	I <sub>F</sub>	1.0	Α
Forward Current Surge Peak (60 Hz, 1 cycle)	I <sub>FSM</sub>	12	Α
Non-Repetitive Peak Forward Current (Square Wave, T <sub>J</sub> = 25°C prior to surge) t = 1 µs t = 1 ms t = 1 s	I <sub>FSM</sub>	40 10 3.0	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. All specifications pertain to a single diode.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T <sub>A</sub> = 25°C	P <sub>D</sub> (Note 2)	1.80	W
Derate above 25°C		18	mW/°C
Thermal Resistance Junction to Ambient	R <sub>θJA</sub> (Note 2)	55.5	°C/W
Total Device Dissipation T <sub>A</sub> = 25°C	P <sub>D</sub> (Note 3)	0.70	W
Derate above 25°C		7.0	mW/°C
Thermal Resistance Junction to Ambient	R <sub>θJA</sub> (Note 3)	142	°C/W
Total Device Dissipation $T_A = 25^{\circ}C$	P <sub>D</sub> (Note 4)	0.80	W
Derate above 25°C		8.0	mW/°C
Thermal Resistance Junction to Ambient	R <sub>θJA</sub> (Note 4)	125	°C/W
Junction Temperature	$T_J$	+125	°C
Storage Temperature Range	T <sub>stg</sub>	–55 to +150	°C

- 4 Layer JEDEC JESD51.7 FR-4 @ 10 mm², 1 oz. copper trace, still air.
   Single Layer JEDEC JESD51.3 FR-4 @ 100 mm², 1 oz. copper trace, still air.
   Single Layer JEDEC JESD51.3 FR-4 @ 100 mm², 2 oz. copper trace, still air.



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#### MARKING **DIAGRAM**



### UDFN4 3x3 CASE 517DB

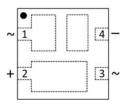


1030 = Specific Device Code Α = Assembly Location

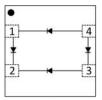
= Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

#### **PIN CONNECTIONS**



## **DEVICE SCHEMATIC**



## **ORDERING INFORMATION**

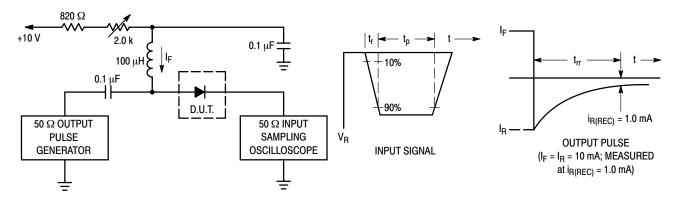
Device	Package	Shipping†
NSR1030QMUTAG	UDFN4 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted) (Note 5)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I <sub>R</sub> = 1.0 mA)	V <sub>(BR)</sub>	30	-	-	V
Reverse Leakage (V <sub>R</sub> = 30 V)	I <sub>R</sub>	-	4.0	20	μΑ
Forward Voltage (I <sub>F</sub> = 0.5 A)	V <sub>F</sub>	-	0.43	0.49	V
Forward Voltage (I <sub>F</sub> = 1.0 A)	V <sub>F</sub>	-	0.49	0.60	V
Reverse Recovery Time $(I_F = I_R = 10 \text{ mA}, I_{R(REC)} = 1.0 \text{ mA})$	t <sub>rr</sub>	-	25	-	ns
Input Capacitance (pins 1 to 3) (V <sub>R</sub> = 1.0 V, f = 1.0 MHz)	C <sub>T</sub>	-	70	-	pF

5. All specifications pertain to a single diode.



Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (IF) of 10 mA.

- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.
- 3.  $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

#### **TYPICAL CHARACTERISTICS**

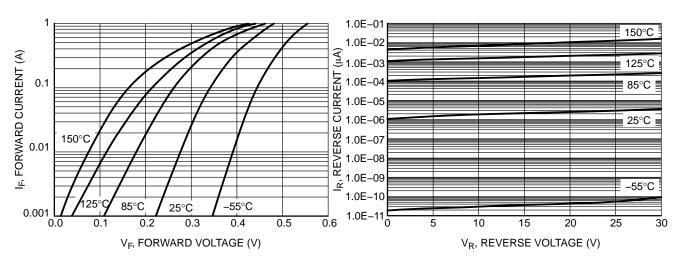


Figure 1. Forward Voltage

Figure 2. Reverse Leakage

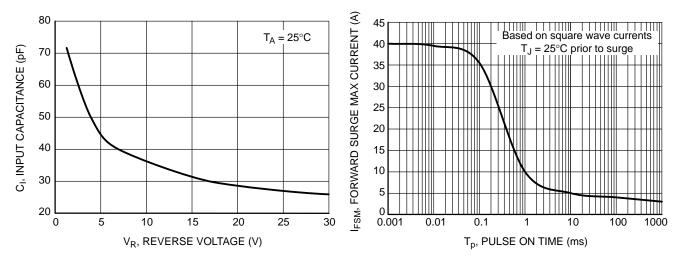


Figure 3. Input Capacitance

Figure 4. Forward Surge Current

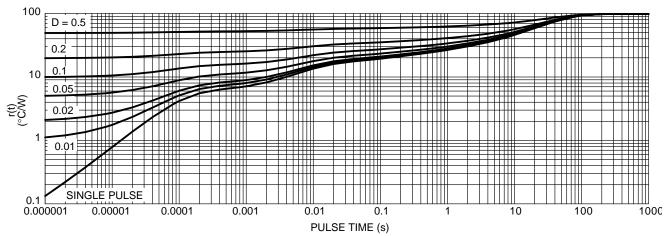
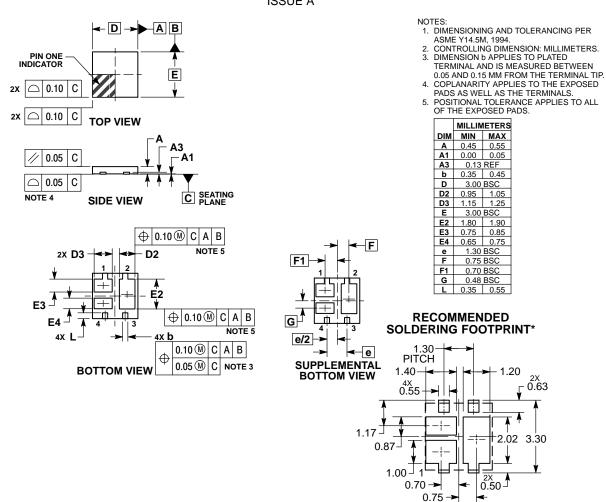


Figure 5. Thermal Response

#### PACKAGE DIMENSIONS

## UDFN4 3.0x3.0, 1.30P CASE 517DB ISSUE A



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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